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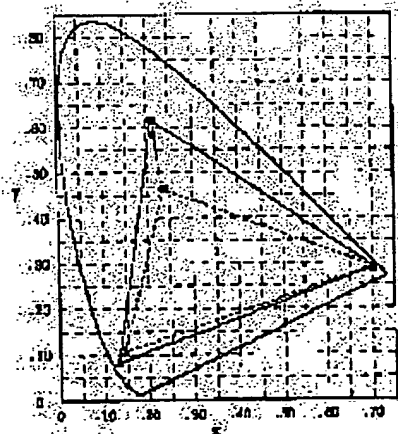
NAGAI YOSHIFUMI

(54) NITRIDE SEMICONDUCTOR LED

(57)Abstract:

PURPOSE: To make narrow the half-width of an LED to improve the color purity of the LED as well as to improve the color expression of the LED in the LED, which uses a nitride semiconductor layer containing impurities as its luminescent center and has a wide half-width.

CONSTITUTION: A nitride semiconductor layer containing impurities as its luminescent center is used as a luminous layer and a nitride semiconductor LED with the luminous layer, whose peak wavelength is between a wavelength of 480nm and a wavelength of 540nm, is provided with an optical filter, whose mean transmittance in a wavelength of 430 to 470nm is 70% or lower, or a nitride semiconductor LED with the luminous layer, whose peak wavelength is between a wavelength of 430nm and a wavelength of 470nm, is provided with an optical filter, whose mean transmittance in a wavelength of 480 to 540nm is 80% or lower.



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